

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

LV8018W

For Portable MD 4ch PWM H-bridge Driver

Overview

The LV8018W is 4-chnnel PWM-drive H-bridge driver for portable MD.

Bi-CMOS IC

Functions

- 4-chnnel PWM-drive H-bridge driver.
- Built-in charge pump circuit.
- Built-in thermal shutdown circuit.

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage (Output block)	VBAT max		7	V
Supply voltage (Control block)	V _{CC} max		7	V
Predrive voltage (gate voltage)	VG max		9.5	V
Maximum output current (ch1-ch4)	I _O max		500	mA
Allowable power dissipation	Pd max	Independent IC	0.5	W
Operating temperature	Topr		-20 to +85	°C
Storage temperature	Tstg		-55 to +150	°C

Operating Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Recommended supply voltage (Output block)	VBAT max		7	V
Recommended supply voltage (Control block)	V _{CC} max		7	V
Predrive voltage (gate voltage)	VG max		9.5	V

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LV8018W

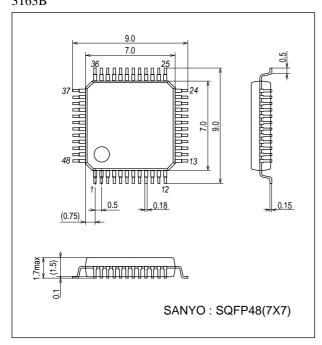
Electrical Characteristics at Ta = 25°C, $V_{CC}1$, 2 = 3.0V, VBAT = 3.0V

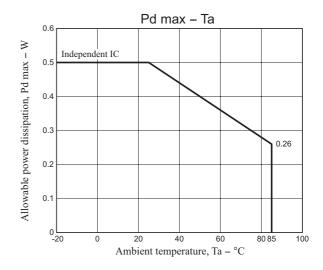
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Parameter	Symbol	Conditions	min	typ	max	Unit	
Standby current dissipation	Icco				10	μА	
Current dissipation	I _{CC} (A)	V _{GOFF} = "L"		1.4	1.9	mA	
	I _{CC} (B)	V _{GOFF} = "H"		1.0	1.5	mA	
Predrive block current	I _{GO}	VG = 7V, each logic input = "L"		70	105	μА	
dissipation	IG	VG = 7, input frequency 88kHz		1.0	1.5	mA	
S/S bias current	ISS	S/S = 3.0V		80	120	μΑ	
S/S input "High" voltage	Vssh		V _{CC} 2-0.6		V _{CC} 1	V	
S/S input "Low" voltage	V _{SSL}		0		0.6	V	
VBATT/2 set voltage accuracy	ΔV_{MON}				±10	%	
VBATT/2 limit voltage	VMONLIM		V _{CC} 1-0.2	V _{CC} 1		V	
VBATT monitor input resistance	R _{MON}		35	50	75	kΩ	
Logic input bias current	I _{LG}				±1	μΑ	
Logic input "High" voltage	VLGH		V _{CC} 2-0.6		V _{CC} 2	V	
Logic input "Low" voltage	V _{LGL}		0		0.6	V	
Booster circuit							
Output voltage	V _{GO}	No load	8.5	8.8		V	
	V _G	I _{GOUT} = -1mA	6.7	7.2		V	
Output oscillation-frequency	Fosc		100	115	130	kHz	
Clamp voltage	VGLIM	V _{GOFF} = "L", V _{CC} 1, 2 = 3.6V	9.2	9.5	9.8	V	
MOS driver output stage (VG = 7V)							
Output ON resistance	Ron1, 2, 3, 4	I _O = 100mA, sum of upper and lower outputs		1.3	2.0	Ω	
Output propagation delay time	TRISE	*		0.2	1.0	μS	
	YFALL	*		0.1	0.7	μS	
Minimum pulse width	Tmin	Output pulse width ≥ (2/3) Tmin *	200			ns	
TSD circuit							
Operating temperature	TSD	*	150	180		°C	
Hysteresis width	ΔTSD	*		30		°C	

^{*: &}quot;Design" indicates the design target, not the measured value.

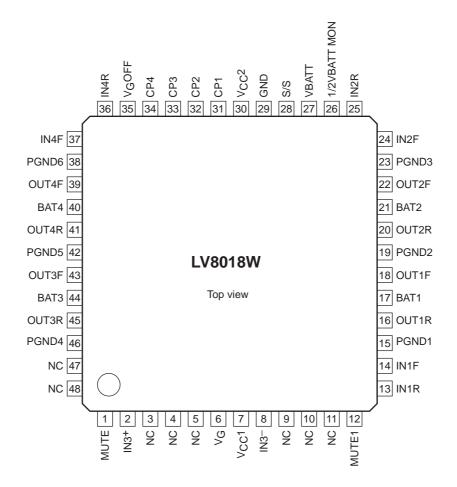
Package Dimensions

unit : mm (typ) 3163B





Pin Assignment



Truth table

Ch1, 2, 4 (for focus, tracking, and traverse)

S/S	MUTE1	IN1, 2, 4F	IN1, 2, 4R	OUT1, 2, 4F	OUT1, 2, 4R
Н	Н	L	L	L	L
Н	Н	Н	L	Н	L
Н	Н	L	Н	L	Н
Н	Н	Н	Н	L	L
Н	L	×	×	Z	Z
L	×	×	×	Z	Z

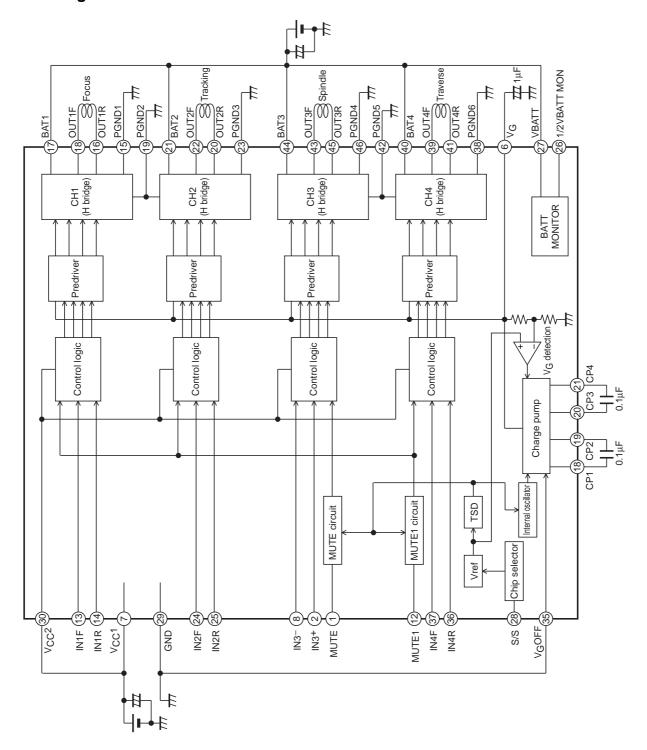
^{×:} Don't Care, Z: Open

Ch3 (for spindle)

S/S	MUTE	IN3+	IN3-	OUT3F	OUT3R
Н	Н	L	L	L	L
Н	Н	Н	L	Н	Г
Н	Н	L	Н	L	L
Н	Н	Н	Н	L	Н
Н	L	×	×	Z	Z
L	×	×	×	Z	Z

 $[\]times$: Don't Care, Z : Open

Block Diagram



^{*} Constants of external parts are for reference and not guaranteed

LV8018W

Pin Functions

Pin No.	Pin neme	Function	Equivalent Circuit
1	MUTE	Channel 3 MUTE pin. L for MUTE ON.	1 - W - CC ² VCC ²
2 8	IN3+ IN3-	Input pins, each on the forward side and reverse side of Channel 3. (Digital input)	2 VCC ² VCC ² 8
6	V _G	Pin to provide the supply voltage to the predrive. With VGOFF = "L", the output voltage of booster circuit is output to this pin. This voltage acts directly as the supply voltage of predrive.	
7	V _{CC} 1	Pin to provide the supply voltage of analog signal system.	
12	MUTE1	MUTE pin common to Channel 1, 2, and 4. L for MUTE ON.	12-W
14 13	IN1F IN1R	Input pins, each on the forward side and reverse sides of Channel 1. (Digital input)	13—W———————————————————————————————————
18 16 17 15 19	OUT1F OUT1R BAT1 PGND1 PGND2	OUT1F: Channel 1 forward side output pin. OUT1R: Channel 1 reverse side output pin. BAT1: Channel 1 output power pin. PGND1, 2: Power GND pin.	Transistor under a neighboring H
22 20 21 23	OUT2F OUT2R BAT2 PGND3	OUT2F: Channel 2 forward side output pin. OUT2R: Channel 2 reverse side output pin. BAT2: Channel 2 output power pin. PGND3: Power GND pin.	Transistor under a neighboring H
24 25	IN2F IN2R	Input pins, each on the forward side and reverse side of Channel 2. (Digital input)	Vcc2 Vcc2 24 W # # # # # # # # # # # # # # # # # #

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Pin No.	Pin neme	Function	Equivalent Circuit
27 26	VBATT 1/2VBATT MON	Output power connection pin Pin to monitor 1/2 of output power supply. Used to monitor the output power supply at the digital servo and to correct the voltage dependence of servo.	Vcc1 27 28 28 28
28	S/S	Start/stop pin. H for start and L for stop.	Vcc1 28 W F M
29	GND	Signal GND pin.	
30	V _{CC} 2	Pin to provide supply voltage of the logic signal system.	
31 32 33 34	CP1 CP2 CP3 CP4	CP1, 3 : Switching pins of booster circuit CP2, 4 : Pins to which the rectifier transistor of booster circuit is connected	32 34 6 7 7 7 7 7 7 7 7 7 7 7 7 7
35	V _G OFF	Booster circuit ON/OFF selector pin. L for booster circuit ON H for booster circuit OFF	35 W 77
37 36	IN4F IN4R	Input pins, each on the forward side and reverse side of Channel 4.	Vcc2 Vcc2 36 W 777
39 41 40 42 38	OUT4F OUT4R BAT4 PGND5 PGND6	OUT4F: Channel 4 forward side output pin. OUT4R: Channel 4 reverse side output pin. BAT4: Channel 4 output power pin. PGND5, 6: Power GND pin.	Transistor under a neighboring H
43 45 44 46	OUT3F OUT3R BAT3 PGND4	OUT3F: Channel 3 forward side output pin. OUT3R: Channel 3 reverse side output pin. BAT3: Channel 3 output power pin. PGND4: Power GND pin.	Transistor under a neighboring H

LV8018W

Cautions for use

- Apply power in the order from V_{CC} to each BAT. When the external power supply is used for V_G, apply power in the order from V_{CC}, through V_G, to each BAT. For each BAT, turn ON power supply after complete rising of V_{CC} and VG voltages.
- 2. Each power supply must be stabilized by inserting a capacitor to GND to prevent entry of ripple and noise. In particular, the capacitor of sufficient capacitance must be used for the output because the large current flows here. The capacitor to be inserted in each power supply should be installed as near as possible to the IC pin.

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